

Title (en)

Memory device supporting a dynamically configurable core organisation

Title (de)

Speicherbaustein, der eine dynamisch konfigurierbare Kernorganisation unterstützt

Title (fr)

Dispositif mémoire supportant une organisation de noyau dynamiquement configurable

Publication

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Application

EP 10190843 A 20030626

Priority

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- US 0320599 W 20030626

Abstract (en)

[origin: US2004019756A1] Described is a memory system in which the memory core organization changes with device width. The number of physical memory banks accessed reduces with device width, resulting in reduced power usage for relatively narrow memory configurations. Increasing the number of logic memory banks for narrow memory widths reduces the likelihood of bank conflicts, and consequently improves speed performance.

IPC 8 full level

G06F 12/04 (2006.01); **G06F 12/06** (2006.01); **G06F 12/08** (2006.01); **G11C 5/00** (2006.01); **G11C 5/04** (2006.01); **G11C 7/10** (2006.01); **G11C 8/00** (2006.01); **G11C 11/408** (2006.01); **G11C 11/4097** (2006.01); **H05K 1/14** (2006.01); **H05K 1/11** (2006.01)

CPC (source: EP US)

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Citation (search report)

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